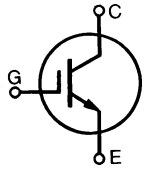
IXYS

HiPerFAST™ IGBT Lightspeed™ Series

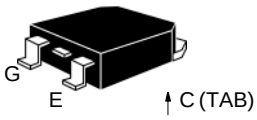
IXGH 32N60C
IXGT 32N60C

V_{CES} = 600 V
I_{C25} = 60 A
$V_{CE(sat)typ}$ = 2.1 V
$t_{fi\ typ}$ = 55 ns

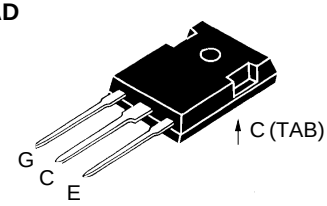


Symbol	Test Conditions	Maximum Ratings	
V_{CES}	T_J = 25°C to 150°C	600	V
V_{CGR}	T_J = 25°C to 150°C; R_{GE} = 1 MΩ	600	V
V_{GES}	Continuous	±20	V
V_{GEM}	Transient	±30	V
I_{C25}	T_C = 25°C	60	A
I_{C110}	T_C = 110°C	32	A
I_{CM}	T_C = 25°C, 1 ms	120	A
SSOA (RBSOA)	V_{GE} = 15 V, T_{VJ} = 125°C, R_G = 10 Ω Clamped inductive load, L = 100 μH	I_{CM} = 64 @ 0.8 V_{CES}	A
P_C	T_C = 25°C	200	W
T_J		-55 ... +150	°C
T_{JM}		150	°C
T_{stg}		-55 ... +150	°C
Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	°C
M_d	Mounting torque (M3)	1.13/10	Nm/lb.in.
Weight	TO-247 AD TO-268	6 4	g g

TO-268 (IXGT)



TO-247 AD (IXGH)



G = Gate, C = Collector,
E = Emitter, TAB = Collector

Symbol	Test Conditions		Characteristic Values (T_J = 25°C, unless otherwise specified) min.	typ.	max.	
BV_{CES}	I_C = 250 μA, V_{GE} = 0 V		600			V
$V_{GE(th)}$	I_C = 250 μA, V_{CE} = V_{GE}		2.5		5	V
I_{CES}	V_{CE} = 0.8 • V_{CES} V_{GE} = 0 V	T_J = 25°C T_J = 150°C			200 1	μA mA
I_{GES}	V_{CE} = 0 V, V_{GE} = ±20 V				±100	nA
$V_{CE(sat)}$	I_C = I_{C110}, V_{GE} = 15 V			2.1	2.5	V

Features

- International standard packages JEDEC TO-247 and surface mountable TO-268
- High current handling capability
- Latest generation HDMOS™ process
- MOS Gate turn-on
  - drive simplicity

Applications

- PFC circuits
- Uninterruptible power supplies (UPS)
- Switched-mode and resonant-mode power supplies
- AC motor speed control
- DC servo and robot drives
- DC choppers

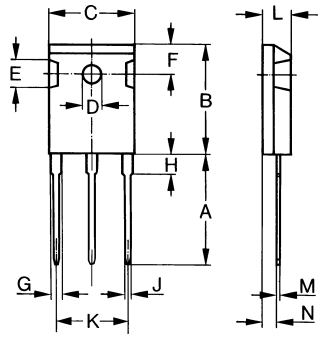
Advantages

- High power density
- Very fast switching speeds for high frequency applications

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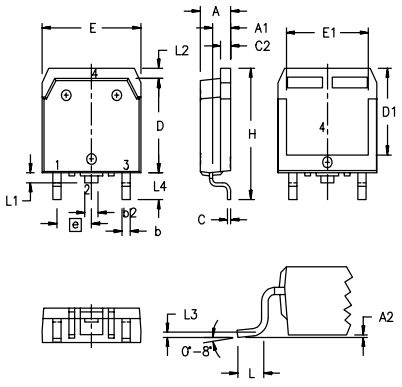
Symbol	Test Conditions (T_J = 25°C, unless otherwise specified)	min.	typ.	max.	
g_{fs}	$I_C = I_{C110}$; V_{CE} = 10 V, Pulse test, t ≤ 300 µs, duty cycle ≤ 2 %		25		S
C_{ies}	V_{CE} = 25 V, V_{GE} = 0 V, f = 1 MHz		2700		pF
C_{oes}			190		pF
C_{res}			50		pF
Q_g	$I_C = I_{C110}$, V_{GE} = 15 V, V_{CE} = 0.5 V_{CES}		110		nC
Q_{ge}			22		nC
Q_{gc}			40		nC
$t_{d(on)}$	**Inductive load, T_J = 25°C**		25		ns
t_{ri}	$I_C = I_{C110}$, V_{GE} = 15 V, L = 100 µH,		20		ns
$t_{d(off)}$	V_{CE} = 0.8 V_{CES}, $R_G = R_{off}$ = 4.7 Ω		85		ns
t_{fi}	Remarks: Switching times may		55		ns
E_{off}	increase for V_{CE} (Clamp) > 0.8 • V_{CES}, higher T_J or increased R_G		0.32		mJ
$t_{d(on)}$	**Inductive load, T_J = 150°C**		25		ns
t_{ri}	$I_C = I_{C110}$, V_{GE} = 15 V, L = 100 µH		25		ns
E_{on}	V_{CE} = 0.8 V_{CES}, $R_G = R_{off}$ = 4.7 Ω		0.30		mJ
$t_{d(off)}$			110	170	ns
t_{fi}	Remarks: Switching times may		105	160	ns
E_{off}	increase for V_{CE} (Clamp) > 0.8 • V_{CES}, higher T_J or increased R_G		0.85	1.25	mJ
R_{thJC}				0.62	K/W
R_{thCK}	(IXGH32N60C)		0.25		K/W

TO-247 AD (IXGH) Outline



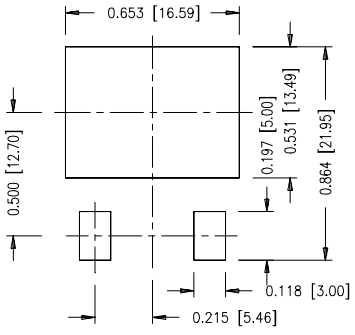
Dim.	Millimeter Min.	Max.	Inches Min.	Max.
A	19.81	20.32	0.780	0.800
B	20.80	21.46	0.819	0.845
C	15.75	16.26	0.610	0.640
D	3.55	3.65	0.140	0.144
E	4.32	5.49	0.170	0.216
F	5.4	6.2	0.212	0.244
G	1.65	2.13	0.065	0.084
H	-	4.5	-	0.177
J	1.0	1.4	0.040	0.055
K	10.8	11.0	0.426	0.433
L	4.7	5.3	0.185	0.209
M	0.4	0.8	0.016	0.031
N	1.5	2.49	0.087	0.102

TO-268AA (D^3 PAK)



Dim.	Millimeter Min.	Max.	Inches Min.	Max.
A	4.9	5.1	.193	.201
A_1	2.7	2.9	.106	.114
A_2	.02	.25	.001	.010
b	1.15	1.45	.045	.057
b_2	1.9	2.1	.75	.83
C	.4	.65	.016	.026
D	13.80	14.00	.543	.551
E	15.85	16.05	.624	.632
E_1	13.3	13.6	.524	.535
e	5.45 BSC		.215 BSC	
H	18.70	19.10	.736	.752
L	2.40	2.70	.094	.106
L1	1.20	1.40	.047	.055
L2	1.00	1.15	.039	.045
L3	0.25 BSC		.010 BSC	
L4	3.80	4.10	.150	.161

Min. Recommended Footprint



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IXYS MOSFETS and IGBTs are covered by one or more of the following U.S. patents:
4,835,592 4,881,106 5,017,508 5,049,961 5,187,117 5,486,715
4,850,072 4,931,844 5,034,796 5,063,307 5,237,481 5,381,025

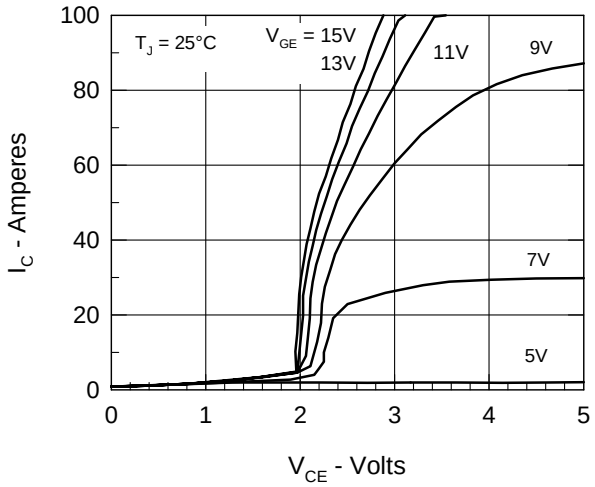


Fig. 1. Output Characteristics

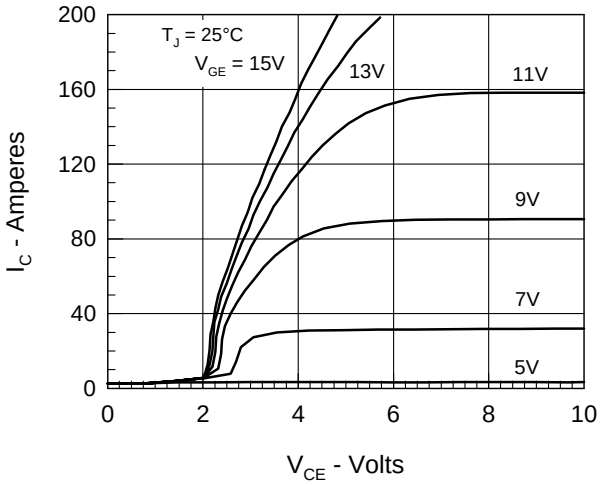


Fig. 2. Extended Output Characteristics

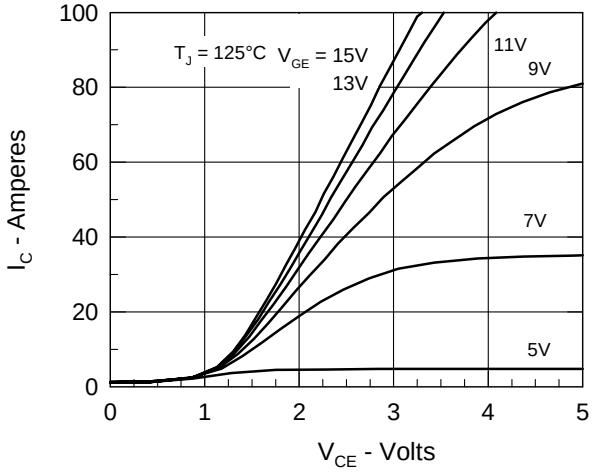


Fig. 3. High Temperature Output Characteristics

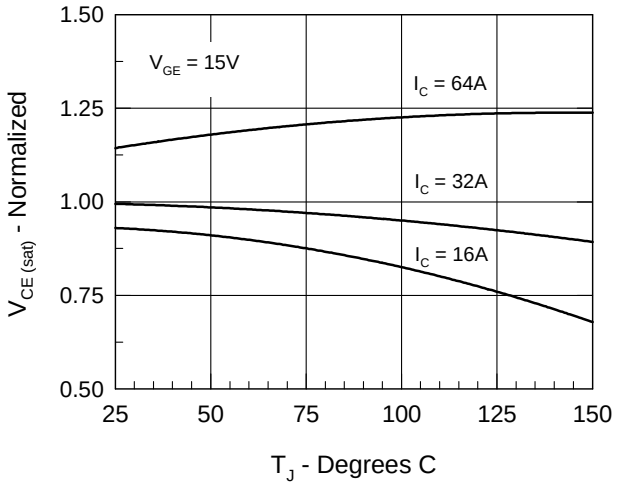


Fig. 4. Temperature Dependence of $V_{CE(sat)}$

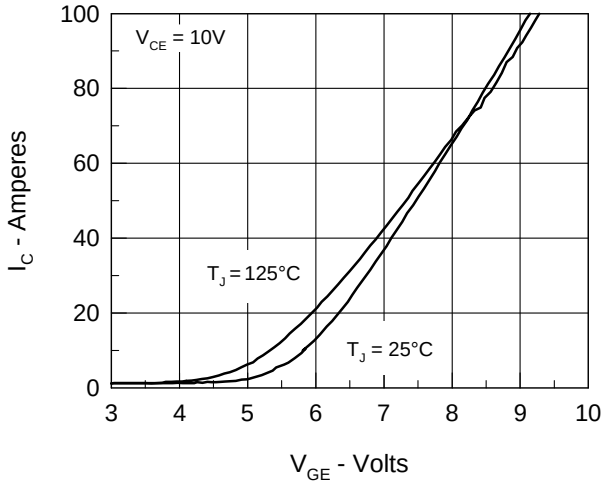


Fig. 5. Admittance Curves

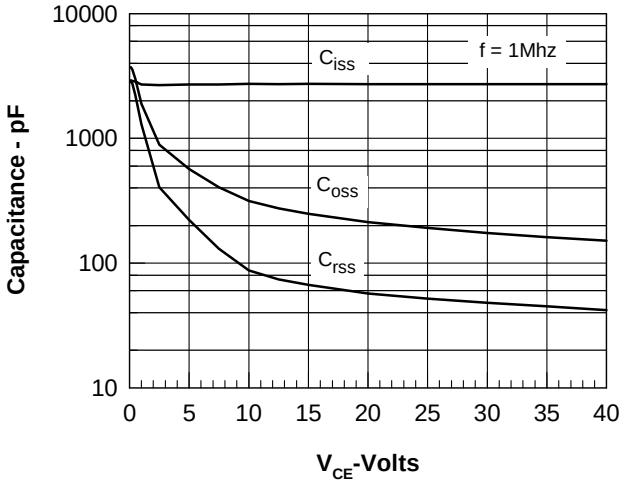


Fig. 6. Capacitance Curves

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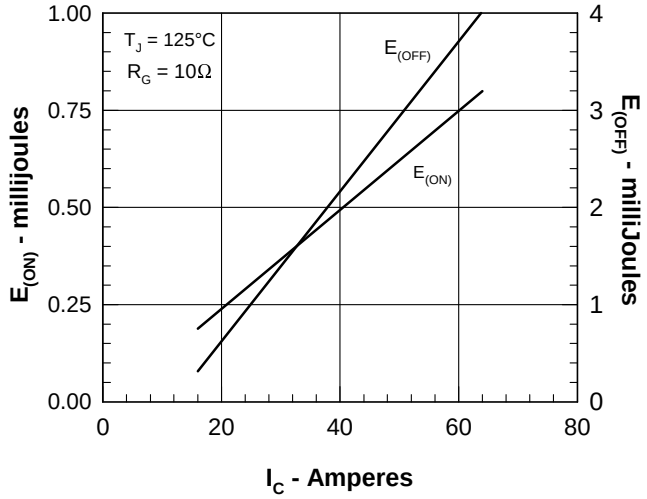


Fig. 7. Dependence of E_{ON} and E_{OFF} on I_C.

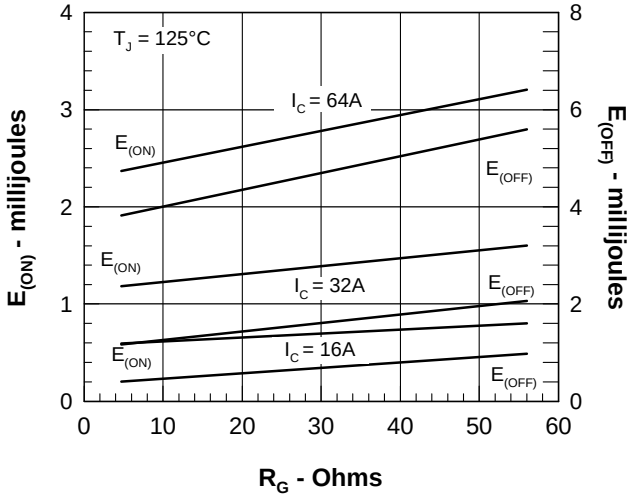


Fig. 8. Dependence of E_{ON} and E_{OFF} on R_G.

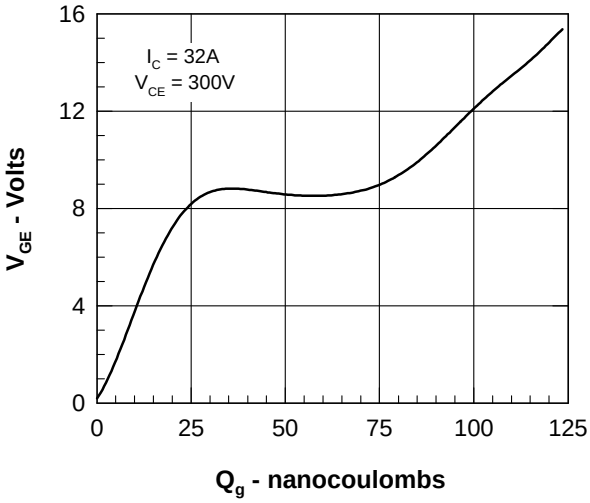


Fig. 9. Gate Charge

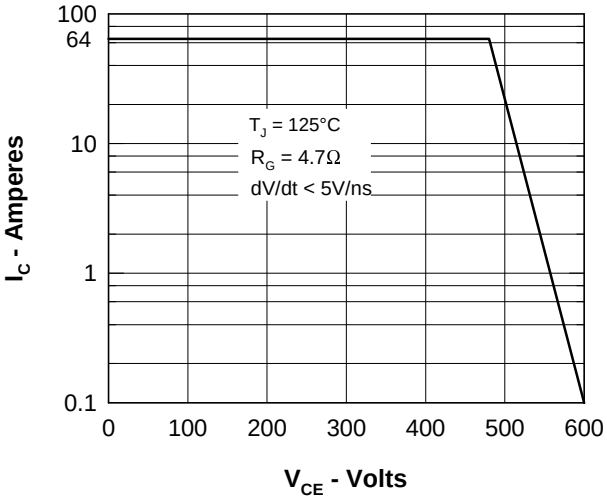


Fig. 10. Turn-off Safe Operating Area

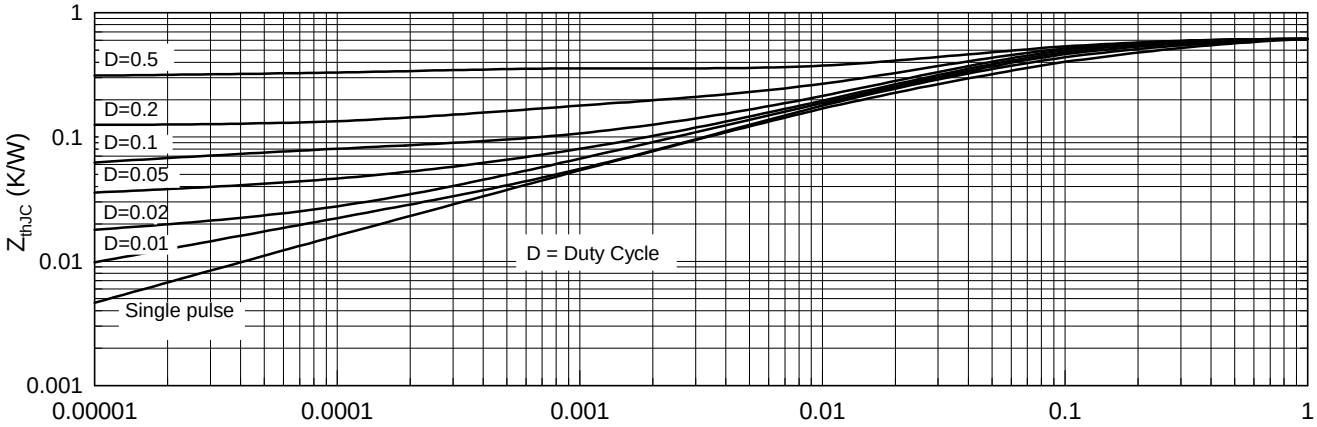


Fig. 11. Transient Thermal Resistance

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